



MOCVD system for Nitride

(Type: SH2001/SH3001/SH4001)

The Features

Wide range growth temperature and reactor pressure control

Optimized gas flow by simulation

Excellent uniformity

High reproducibility

High reliability

Specifications

Substrate Size: 1X2" Wafer(SH2001)

1X3" Wafer(SH3001)

1X4" Wafer (SH4001)

Reactor: Horizontal type

Resistance heating: Max.1200

View



EpiQuest, Inc.

51 nakagawara, kamitoba, minami-ku, Kyoto-shi, 601-8142 Japan

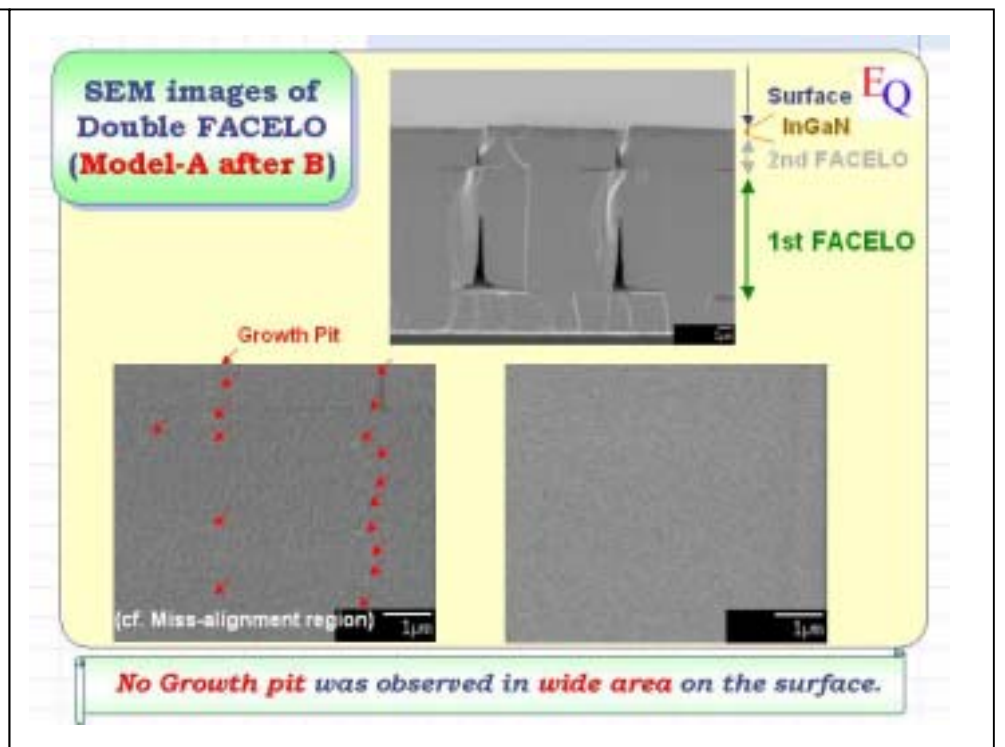
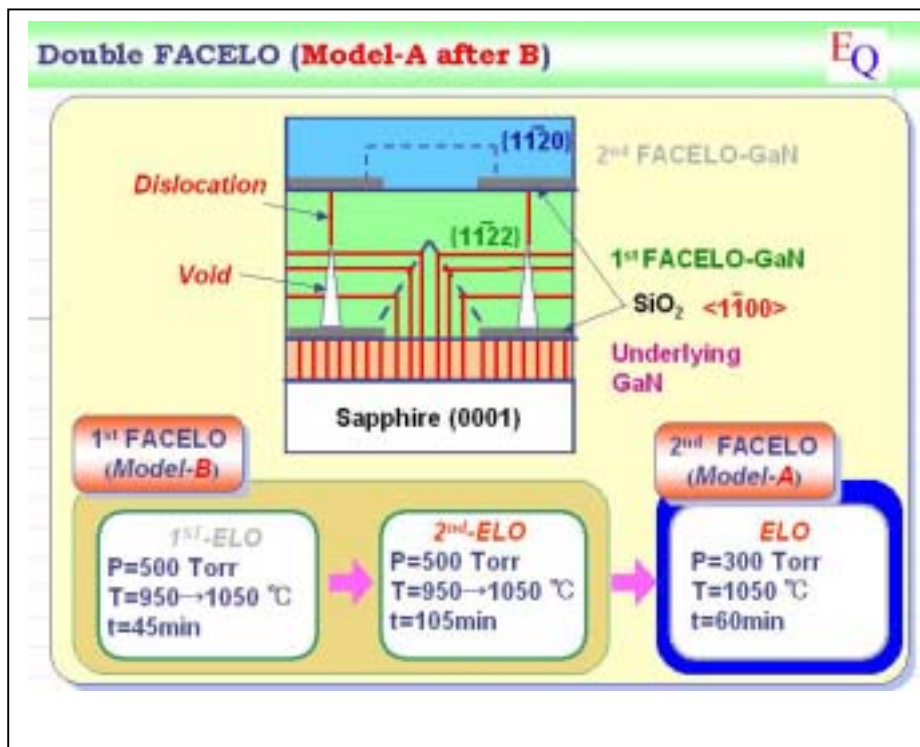
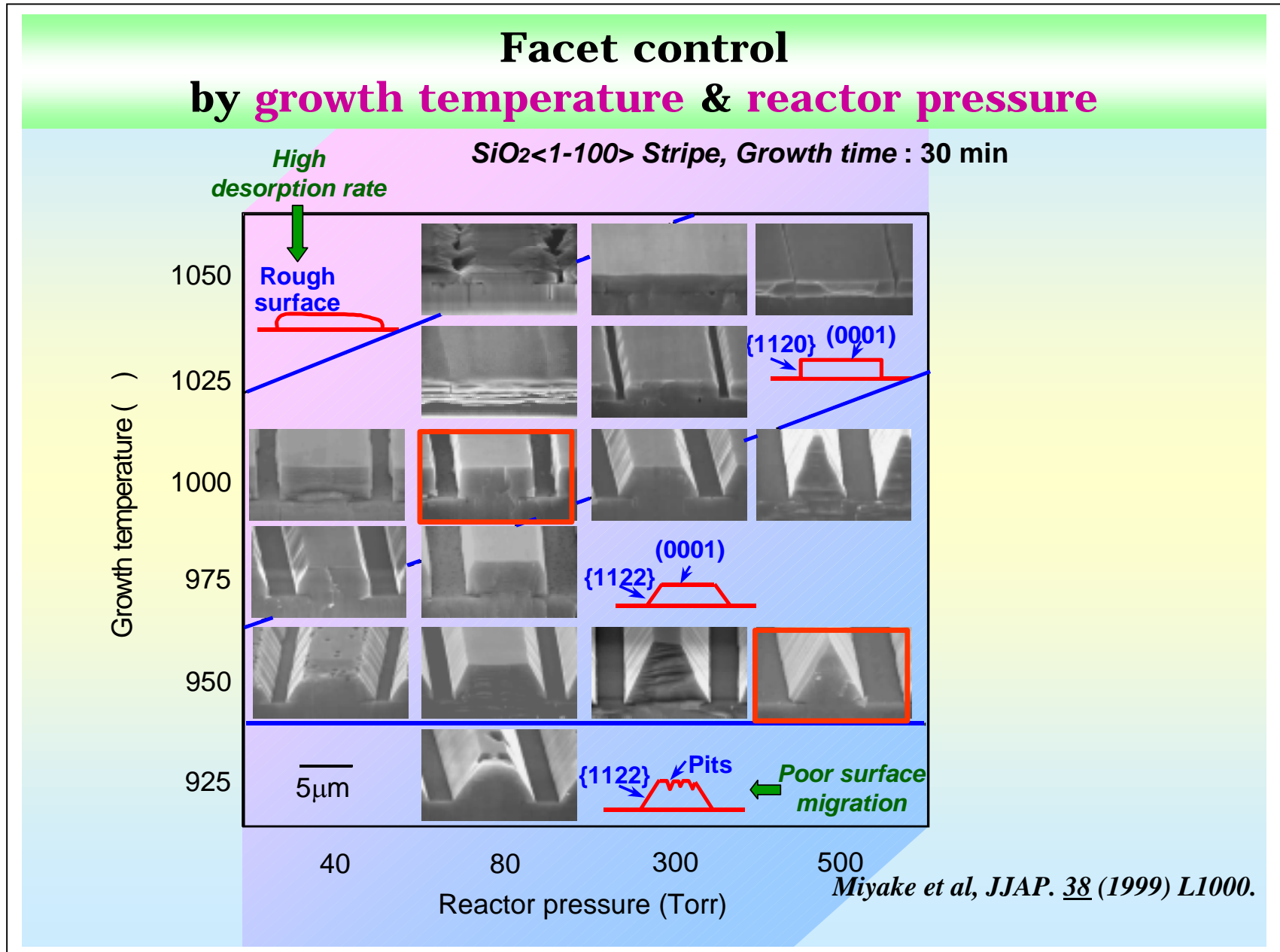
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The Data



These data were provided by Dr.K.Hiramatsu and Dr.H.Miyake of Mie University.

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